SIPMOS® Small-Signal-Transistor

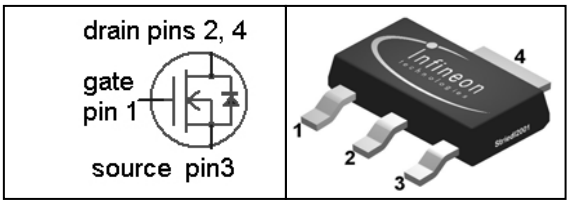
Features

- N-channel
- Depletion mode
- d*v*/d*t* rated

Product Summary

V_{DS}	200	V
$R_{DS(on),max}$	3.5	Ω
$I_{DSS,min}$	0.14	A

SOT-223



Type	Package	Ordering Code	Tape and Reel Information	Marking
BSP149	SOT-223	Q67000-S071	E6327: 1000 pcs/reel	BSP149

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	T_A=25 °C	0.66	A
		T_A=70 °C	0.53	
Pulsed drain current	$I_{D,pulse}$	T_A=25 °C	2.6	
Reverse diode d*v*/d*t*	d*v*/d*t*	I_D=0.66 A, V_{DS}=160 V, d*i*/d*t*=200 A/µs, $T_{j,max}$=150 °C	6	kV/µs
Gate source voltage	V_{GS}		±20	V
ESD sensitivity (HBM) as per MIL-STD 883			Class 1	
Power dissipation	P_{tot}	T_A=25 °C	1.8	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 150	°C
IEC climatic category; DIN IEC 68-1			55/150/56	

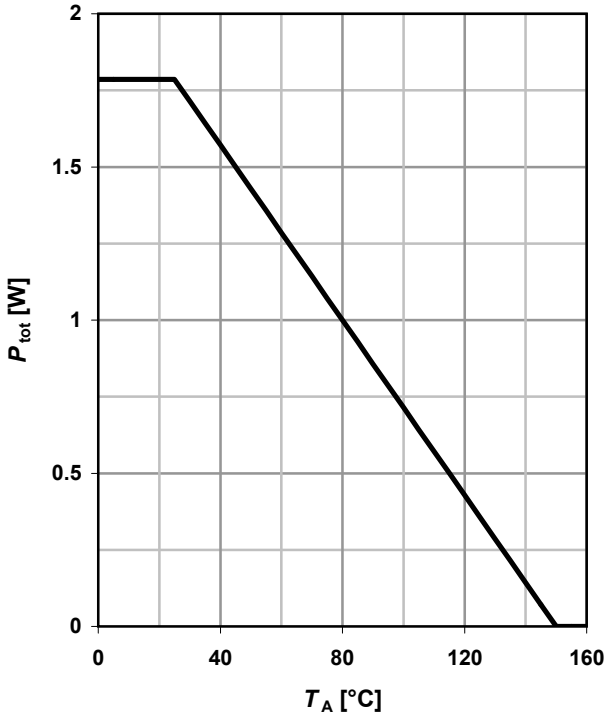
Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - soldering point (pin 4)	R_{thJS}		-	-	25	K/W
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	115	
		6 cm^2 cooling area[1)]	-	-	70	
Electrical characteristics, at T_j=25 °C, unless otherwise specified						
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=-3 V, I_D=250 µA	200	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=3 V, I_D=400 µA	-2.1	-1.4	-1	
Drain-source leakage current	$I_{D\ (off)}$	V_{DS}=200 V, V_{GS}=-3 V, T_j=25 °C	-	-	0.1	µA
		V_{DS}=200 V, V_{GS}=-3 V, T_j=125 °C	-	-	5	
Gate-source leakage current	I_{GSS}	V_{GS}=20 V, V_{DS}=0 V	-	-	10	nA
Saturated drain current	I_{DSS}	V_{GS}=0 V, V_{DS}=10 V	140	-	-	mA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=0 V, I_D=70 mA	-	1.7	3.5	Ω
		V_{GS}=10 V, I_D=660 mA	-	1.0	1.8	
Transconductance	g_{fs}	$\|V_{DS}\|>2\|I_D\|R_{DS(on)max}$, I_D=0.48 A	0.4	0.8	-	S

[1)] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm^2 (single layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics						
Input capacitance	C_{iss}	V_{GS}=-3 V, V_{DS}=25 V, f=1 MHz	-	326	430	pF
Output capacitance	C_{oss}		-	41	55	
Reverse transfer capacitance	C_{rss}		-	17	25	
Turn-on delay time	$t_{d(on)}$	V_{DD}=100 V, V_{GS}=-2…7 V, I_D=0.50 A, R_G=6 Ω	-	5.1	7.7	ns
Rise time	t_r		-	3.4	5.1	
Turn-off delay time	$t_{d(off)}$		-	45	68	
Fall time	t_f		-	21	31	
Gate Charge Characteristics						
Gate to source charge	Q_{gs}	V_{DD}=160 V, I_D=0.05 A, V_{GS}=-3 to 5 V	-	0.74	1.0	nC
Gate to drain charge	Q_{gd}		-	5.6	8.4	
Gate charge total	Q_g		-	11	14	
Gate plateau voltage	$V_{plateau}$		-	0.16	-	V
Reverse Diode						
Diode continous forward current	I_S	T_A=25 °C	-	-	0.66	A
Diode pulse current	$I_{S,pulse}$		-	-	2.6	
Diode forward voltage	V_{SD}	V_{GS}=-3 V, I_F=0.66 A, T_j=25 °C	-	0.9	1.2	V
Reverse recovery time	t_{rr}	V_R=100 V, I_F=0.5 A, di_F/dt=100 A/µs	-	42	65	ns
Reverse recovery charge	Q_{rr}		-	60	90	nC

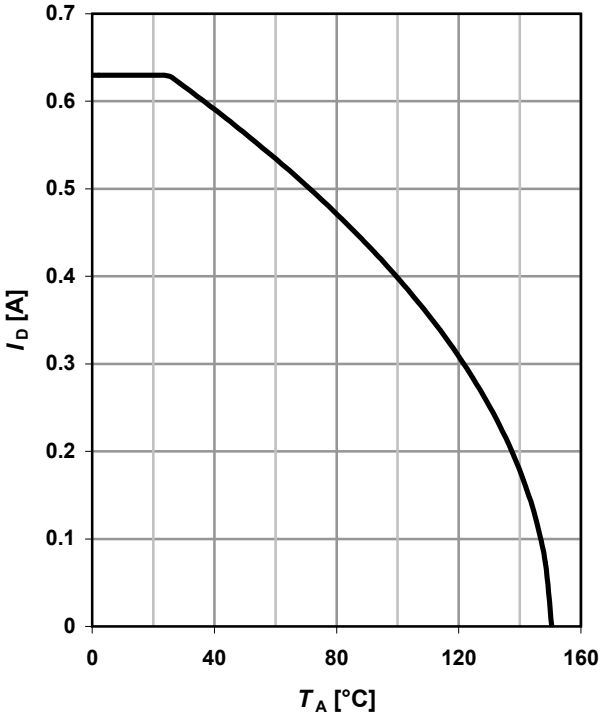
1 Power dissipation

$P_{tot}=f(T_A)$



2 Drain current

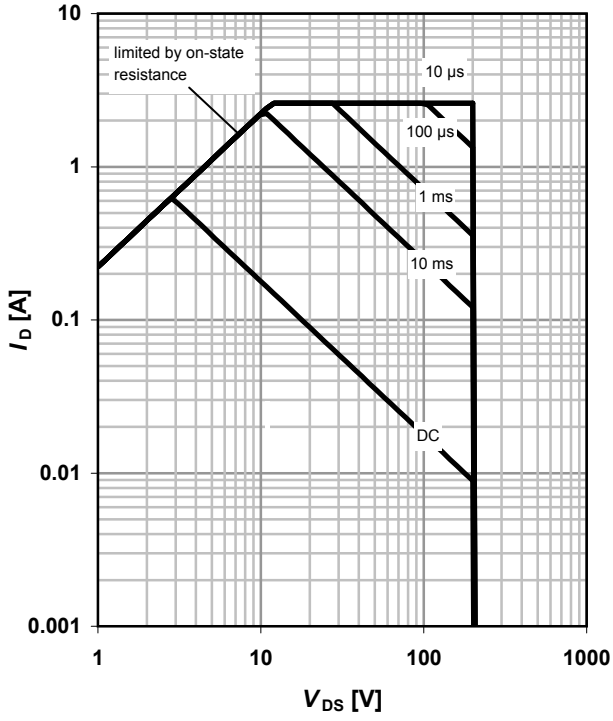
$I_D=f(T_A)$; $V_{GS}\geq 10$ V



3 Safe operation area

$I_D=f(V_{DS})$; T_A=25 °C; D=0

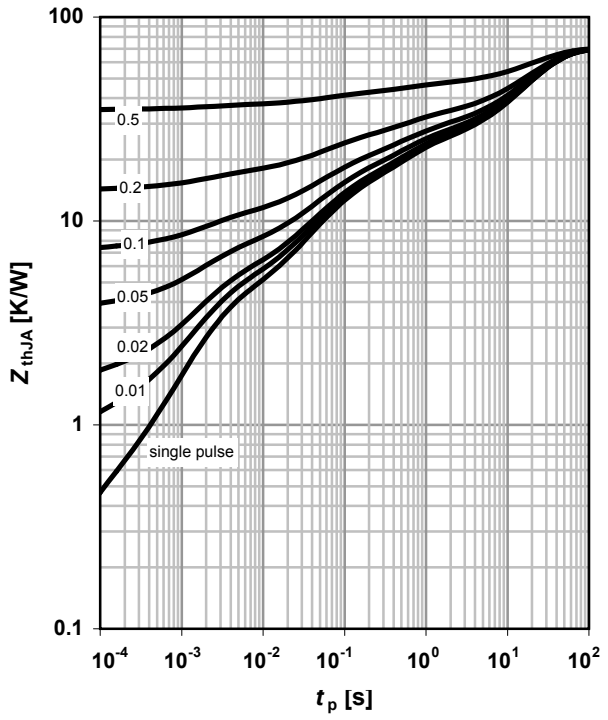
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJA}=f(t_p)$

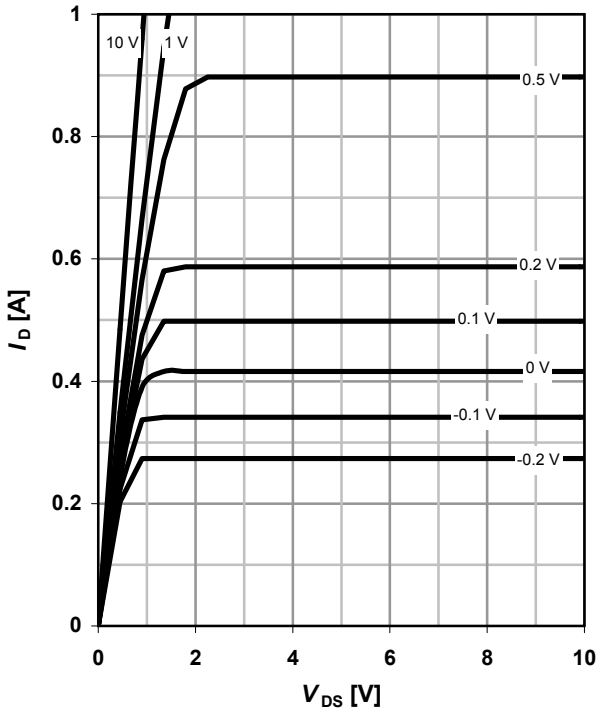
parameter: $D=t_p/T$



5 Typ. output characteristics

I_D=f(V_{DS}); T_j=25 °C

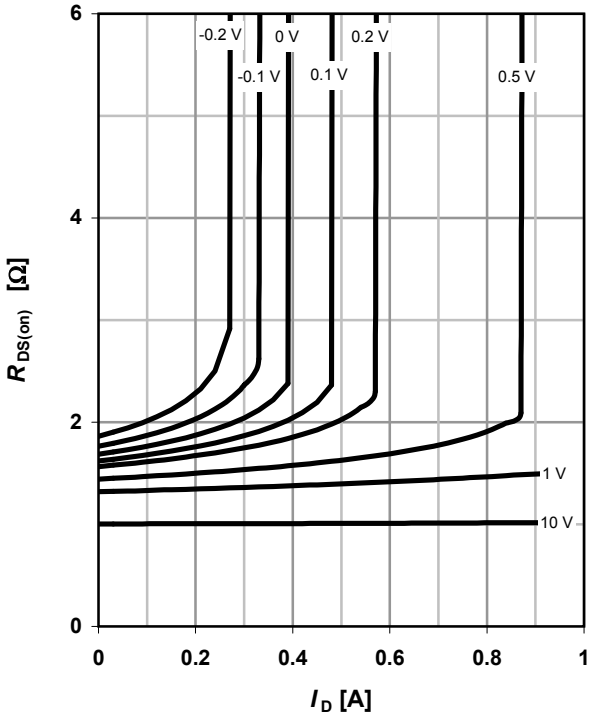
parameter: V_{GS}



6 Typ. drain-source on resistance

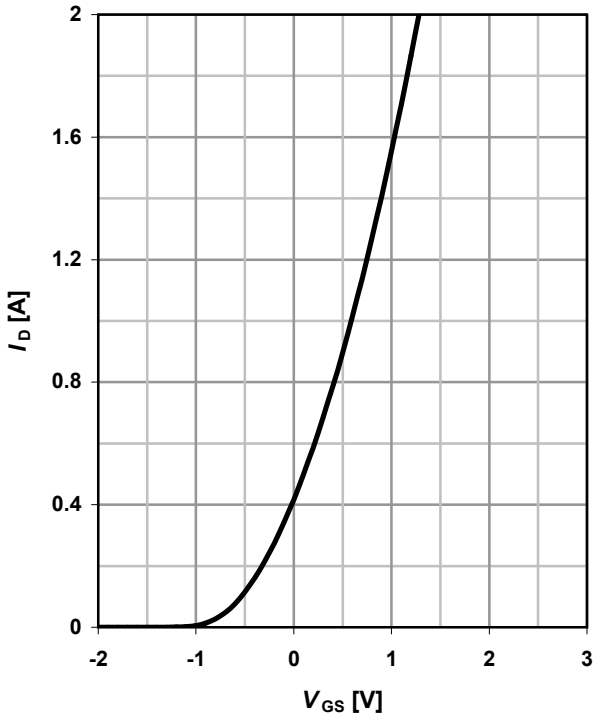
$R_{DS(on)}$=f(I_D); T_j=25 °C

parameter: V_{GS}



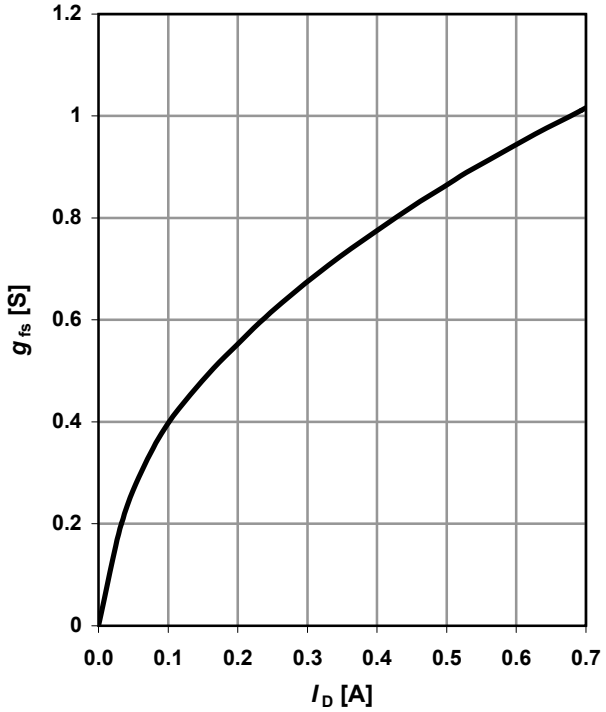
7 Typ. transfer characteristics

I_D=f(V_{GS}); $|V_{DS}|>2|I_D|R_{DS(on)max}$



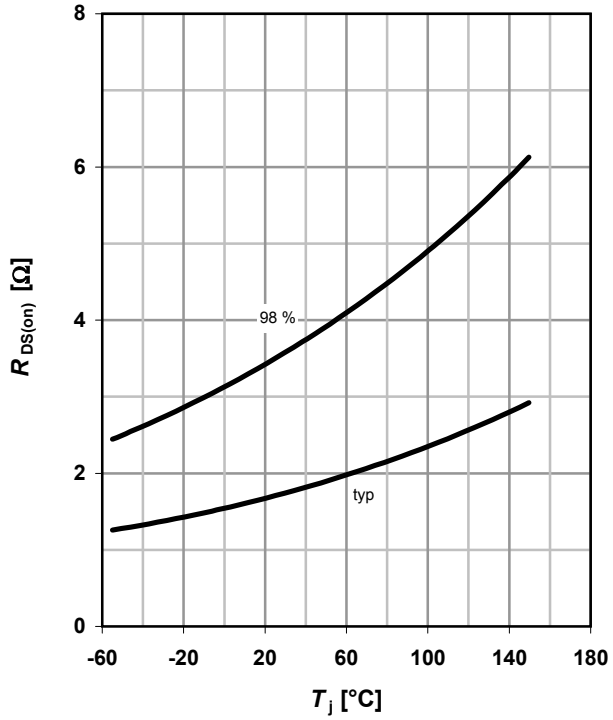
8 Typ. forward transconductance

g_{fs}=f(I_D); T_j=25 °C



9 Drain-source on-state resistance

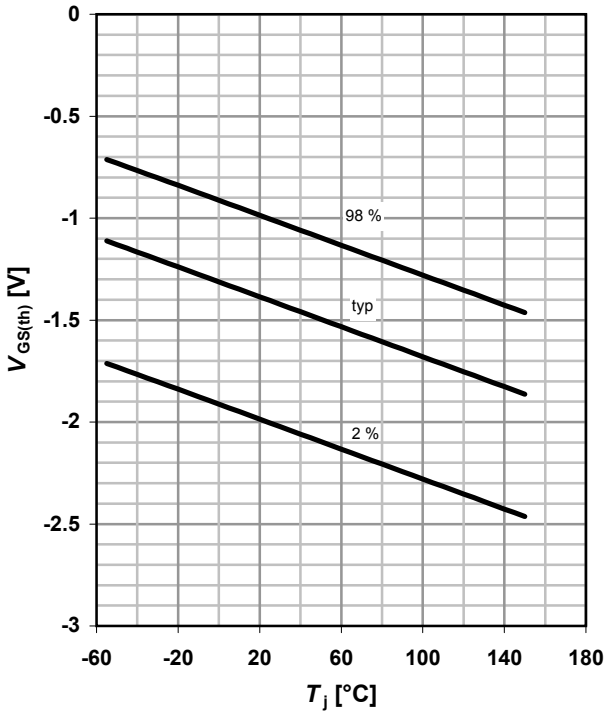
$R_{DS(on)}$=f(T_j); I_D=0.07 A; V_{GS}=0 V



10 Typ. gate threshold voltage

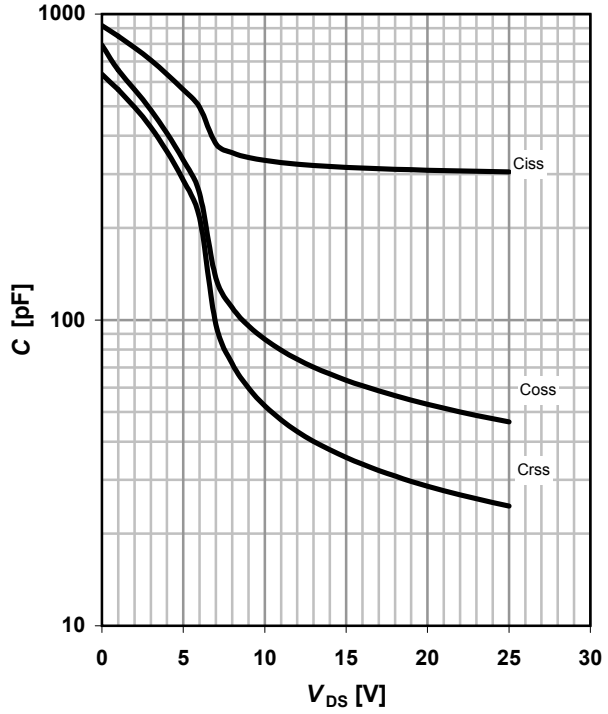
$V_{GS(th)}$=f(T_j); V_{DS}=3 V; I_D=400 µA

parameter: I_D



11 Typ. Capacitances

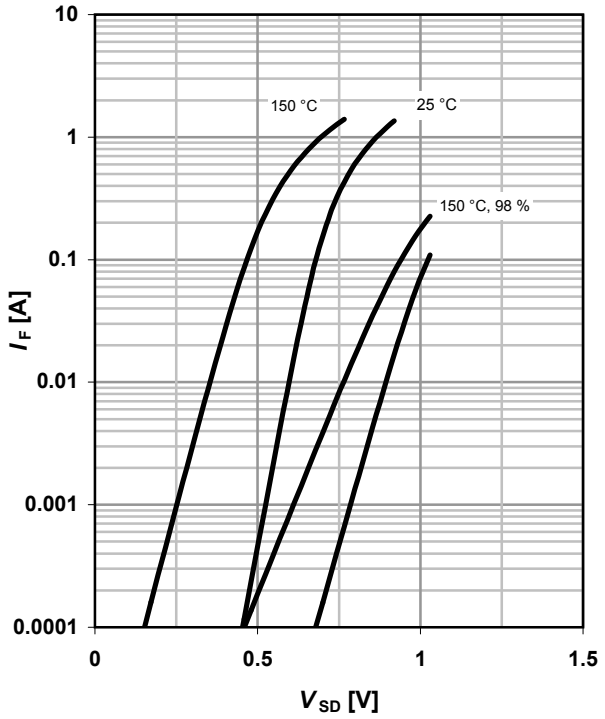
C=f(V_{DS}); V_{GS}=-3 V; f=1 MHz



12 Forward characteristics of reverse diode

I_F=f(V_{SD})

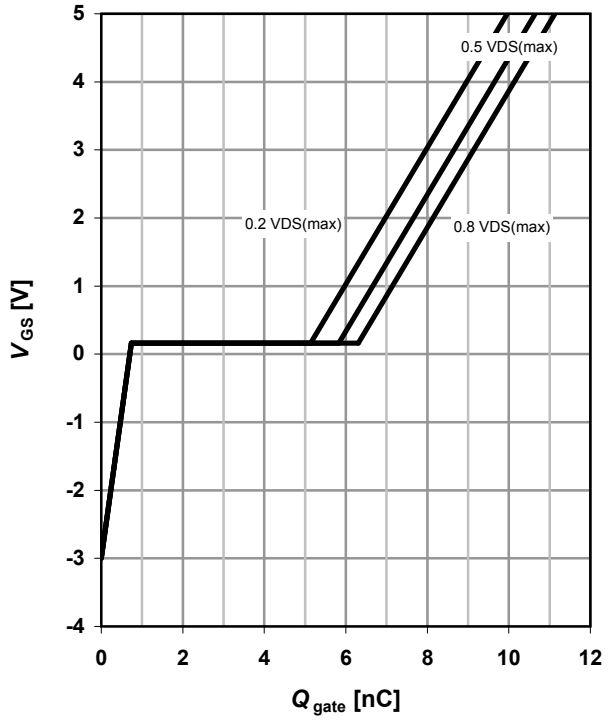
parameter: T_j



14 Typ. gate charge

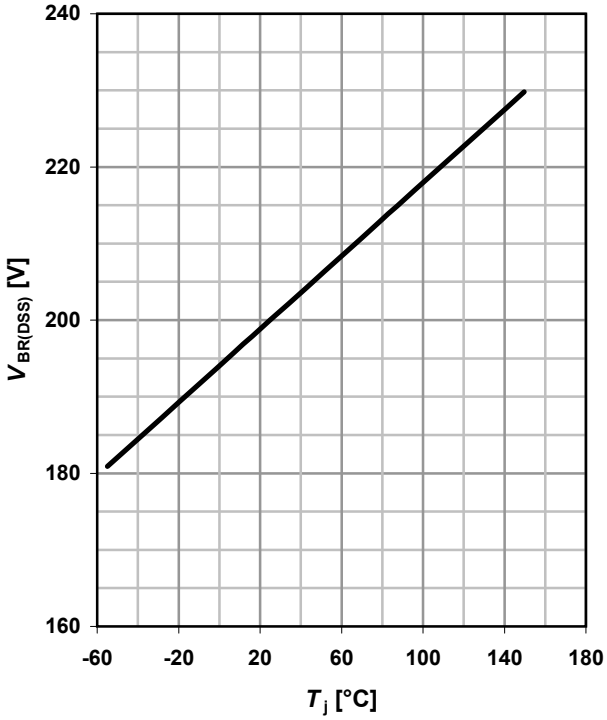
V_{GS}=f(Q_{gate}); I_D=0.5 A pulsed

parameter: V_{DD}

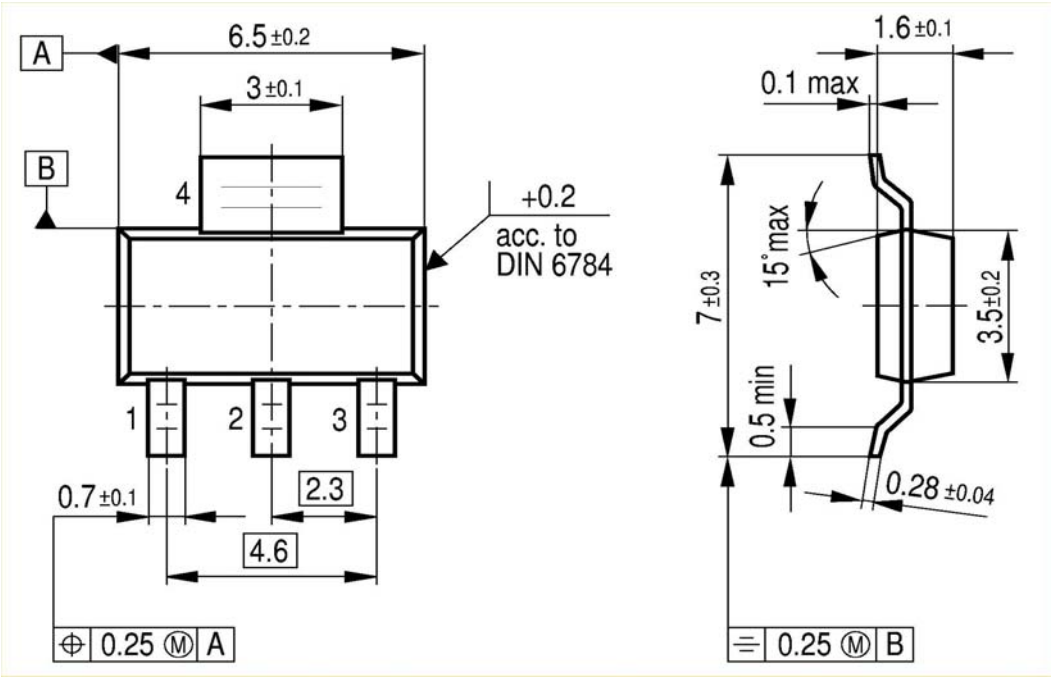


15 Drain-source breakdown voltage

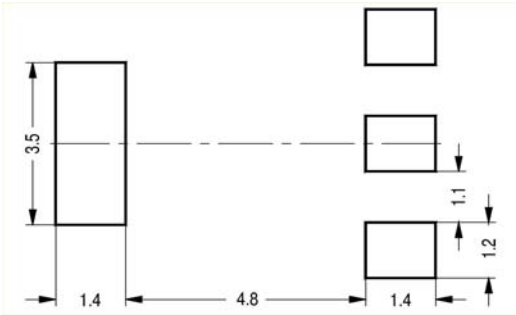
$V_{BR(DSS)}$=f(T_j); I_D=250 µA



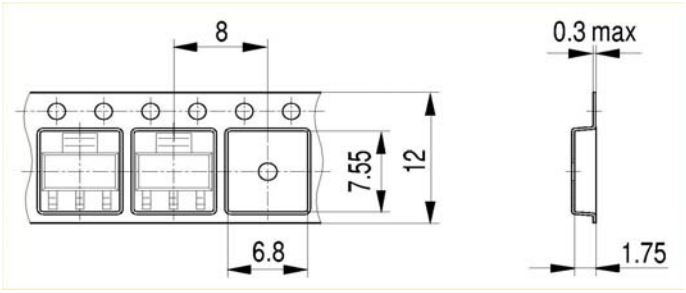
Package Outline:



Footprint:



Packaging:



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